

December 1992

## CMOS Quad Exclusive-OR Gate

### Features

- High Voltage Type (20V Rating)
- Medium-Speed Operation
  - $t_{PHL}, t_{PLH} = 65\text{ns (typ)}$  at  $V_{DD} = 10\text{V}$ ,  $C_L = 50\text{pF}$
- 100% Tested for Quiescent Current at 20V
- Standardized Symmetrical Output Characteristics
- 5V, 10V and 15V Parametric Ratings
- Maximum Input Current Of  $1\mu\text{A}$  at 18V Over Full Package-Temperature Range;
  - $100\text{nA}$  at 18V and  $+25^\circ\text{C}$
- Noise Margin (Over Full Package Temperature Range):
  - 1V at  $V_{DD} = 5\text{V}$
  - 2V at  $V_{DD} = 10\text{V}$
  - 2.5V at  $V_{DD} = 15\text{V}$
- Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

### Applications

- Even and Odd-Parity Generators and Checkers
- Logical Comparators
- Adders/Subtractors
- General Logic Functions

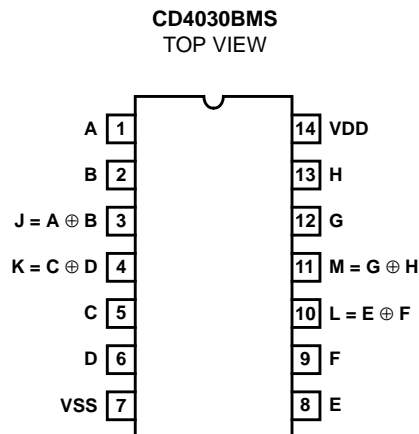
### Description

The CD4030BMS types consist of four independent Exclusive-OR gates. The CD4030BMS provides the system designer with a means for direct implementation of the Exclusive-OR function.

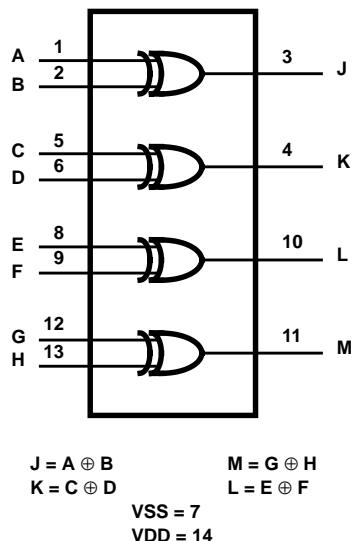
The CD4030BMS is supplied in these 14-lead outline packages:

Braze Seal DIP    H4H  
Frit Seal DIP     H1B  
Ceramic Flatpack H3W

### Pinout



### Functional Diagram



# Specifications CD4030BMS

## Absolute Maximum Ratings

DC Supply Voltage Range, (VDD) ..... -0.5V to +20V  
(Voltage Referenced to VSS Terminals)  
Input Voltage Range, All Inputs ..... -0.5V to VDD +0.5V  
DC Input Current, Any One Input .....  $\pm 10\text{mA}$   
Operating Temperature Range ..... -55°C to +125°C  
Package Types D, F, K, H  
Storage Temperature Range (TSTG) ..... -65°C to +150°C  
Lead Temperature (During Soldering) ..... +265°C  
At Distance 1/16  $\pm$  1/32 Inch (1.59mm  $\pm$  0.79mm) from case for  
10s Maximum

## Reliability Information

Thermal Resistance .....  $\theta_{ja}$   $\theta_{jc}$   
Ceramic DIP and FRIT Package ..... 80°C/W 20°C/W  
Flatpack Package ..... 70°C/W 20°C/W  
Maximum Package Power Dissipation (PD) at +125°C  
For TA = -55°C to +100°C (Package Type D, F, K) ..... 500mW  
For TA = +100°C to +125°C (Package Type D, F, K) ..... Derate  
Linearity at 12mW/°C to 200mW  
Device Dissipation per Output Transistor ..... 100mW  
For TA = Full Package Temperature Range (All Package Types)  
Junction Temperature ..... +175°C

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1)		GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
						MIN	MAX	
Supply Current	IDD	VDD = 20V, VIN = VDD or GND		1	+25°C	-	2	$\mu\text{A}$
				2	+125°C	-	200	$\mu\text{A}$
		VDD = 18V, VIN = VDD or GND		3	-55°C	-	2	$\mu\text{A}$
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load		1, 2, 3	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH15	VDD = 15V, No Load (Note 3)		1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V		1	+25°C	0.53	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V		1	+25°C	1.4	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V		1	+25°C	3.5	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	+25°C	-	-0.53	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V		1	+25°C	-	-1.8	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V		1	+25°C	-	-1.4	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V		1	+25°C	-	-3.5	mA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10 $\mu\text{A}$		1	+25°C	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10 $\mu\text{A}$		1	+25°C	0.7	2.8	V
Functional	F	VDD = 2.8V, VIN = VDD or GND		7	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 20V, VIN = VDD or GND		7	+25°C			
		VDD = 18V, VIN = VDD or GND		8A	+125°C			
		VDD = 3V, VIN = VDD or GND		8B	-55°C			
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	-	4	V
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	11	-	V

NOTES: 1. All voltages referenced to device GND, 100% testing being implemented.  
2. Go/No Go test with limits applied to inputs.  
3. For accuracy, voltage is measured differentially to VDD. Limit is 0.050V max.

# Specifications CD4030BMS

**TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS**

PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Propagation Delay	TPHL TPLH	VDD = 5V, VIN = VDD or GND	9	+25°C	-	280	ns
			10, 11	+125°C, -55°C	-	378	ns
Transition Time	TTHL TTLH	VDD = 5V, VIN = VDD or GND	9	+25°C	-	200	ns
			10, 11	+125°C, -55°C	-	270	ns

**NOTES:**

1. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

**TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS**

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	1	μA
				+125°C	-	30	μA
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	2	μA
				+125°C	-	60	μA
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	2	μA
				+125°C	-	120	μA
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	0.36	-	mA
				-55°C	0.64	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA
				-55°C	1.6	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA
				-55°C	4.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA
				-55°C	-	-0.64	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA
				-55°C	-	-2.0	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-0.9	mA
				-55°C	-	-1.6	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA
				-55°C	-	-4.2	mA
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	7	-	V
Propagation Delay	TPHL TPLH	VDD = 10V	1, 2, 3	+25°C	-	130	ns
		VDD = 15V	1, 2, 3	+25°C	-	100	ns

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**TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)**

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Transition Time	TTHL TTLH	VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	80	ns
Input Capacitance	CIN	Any Input	1, 2	+25°C	-	7.5	pF

NOTES:

1. All voltages referenced to device GND.
2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

**TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS**

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	7.5	μA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10μA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 3V, VIN = VDD or GND					
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

- NOTES: 1. All voltages referenced to device GND. 2. CL = 50pF, RL = 200K, Input TR, TF < 20ns. 3. See Table 2 for +25°C limit. 4. Read and Record

**TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C**

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-1	IDD	± 0.2μA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

**TABLE 6. APPLICABLE SUBGROUPS**

CONFORMANCE GROUP	MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 1 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)	100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)	100% 5004	1, 7, 9, Deltas	
Final Test	100% 5004	2, 3, 8A, 8B, 10, 11	
Group A	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	

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TABLE 6. APPLICABLE SUBGROUPS (Continued)

CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample 5005	1, 7, 9	
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2, 3

NOTE: 1. 5% Parametric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

CONFORMANCE GROUPS	MIL-STD-883 METHOD	TEST		READ AND RECORD	
		PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4

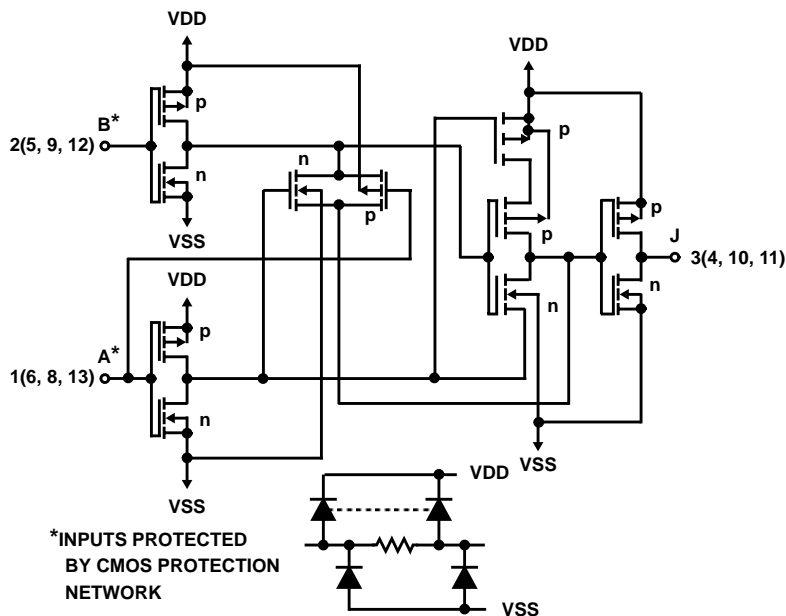
TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

FUNCTION	OPEN	GROUND	VDD	9V $\pm$ -0.5V	OSCILLATOR	
					50kHz	25kHz
Static Burn-In 1 Note 1	3, 4, 10, 11	1, 2, 5 - 9, 12, 13	14			
Static Burn-In 2 Note 1	3, 4, 10, 11	7	1, 2, 5, 6, 8, 9, 12 - 14			
Dynamic Burn-In Note 1	-	7	14	3, 4, 10, 11	2, 6, 9, 13	1, 5, 8, 12
Irradiation Note 2	3, 4, 10, 11	7	1, 2, 5, 6, 8, 9, 12 - 14			

NOTE:

- Each pin except VDD and GND will have a series resistor of  $10K \pm 5\%$ , VDD =  $18V \pm 0.5V$
- Each pin except VDD and GND will have a series resistor of  $47K \pm 5\%$ ; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD =  $10V \pm 0.5V$

## Schematic Diagram



TRUTH TABLE FOR 1 OF 4 IDENTICAL GATES

A	B	J
0	0	0
1	0	1
0	1	1
1	1	0

1 = High Level

0 = Low Level

FIGURE 1. 1 OF 4 IDENTICAL GATES

## Typical Performance Characteristics

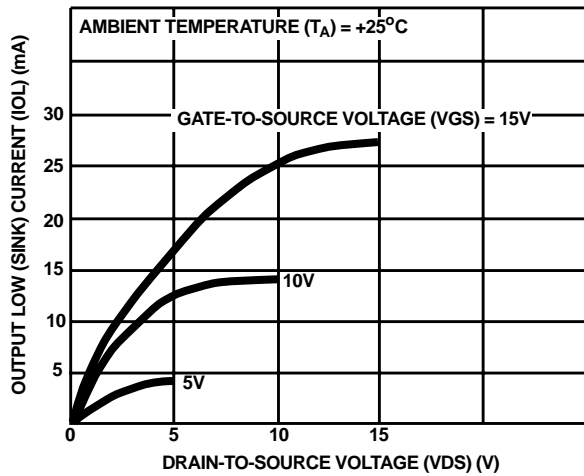


FIGURE 2. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

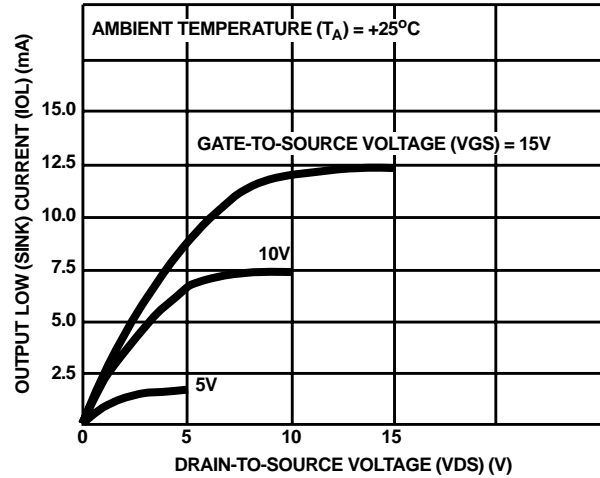


FIGURE 3. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

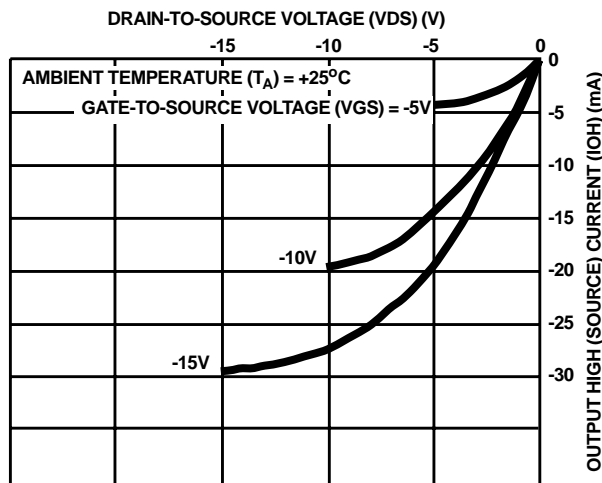


FIGURE 4. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

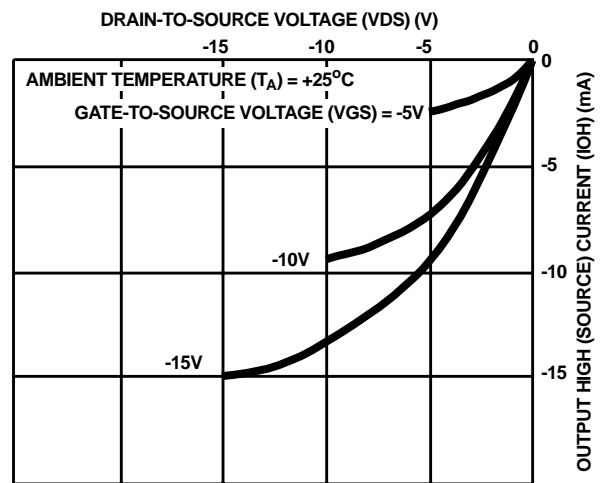


FIGURE 5. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

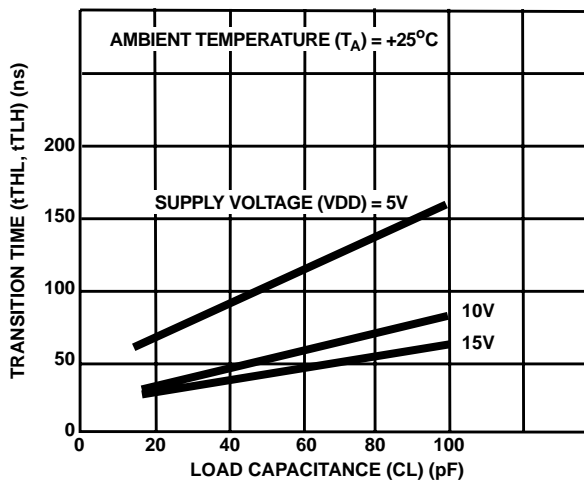


FIGURE 6. TYPICAL TRANSITION TIME AS A FUNCTION OF LOAD CAPACITANCE

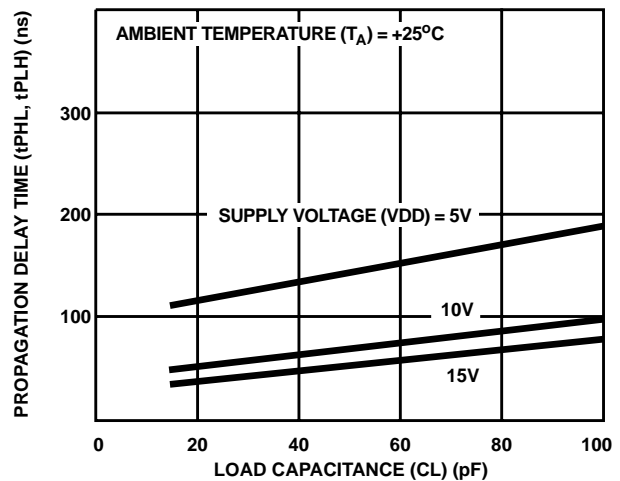


FIGURE 7. TYPICAL PROPAGATION DELAY TIME AS A FUNCTION OF LOAD CAPACITANCE

### Typical Performance Characteristics (Continued)

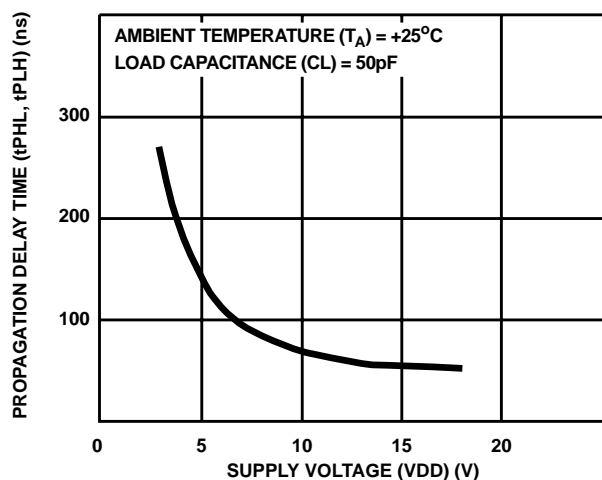


FIGURE 8. TYPICAL PROPAGATION DELAY TIME AS A FUNCTION OF SUPPLY VOLTAGE

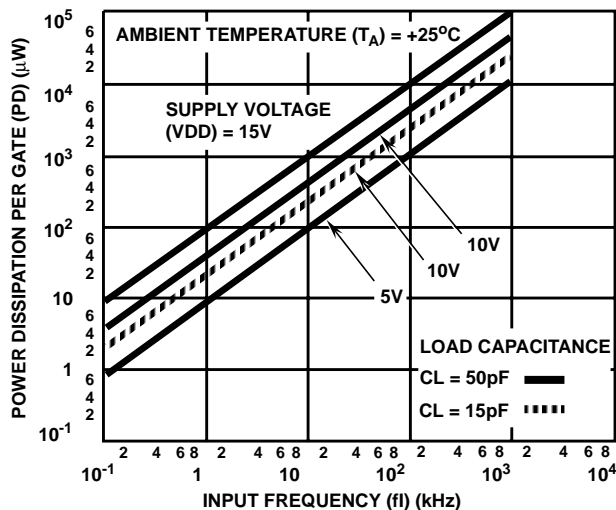
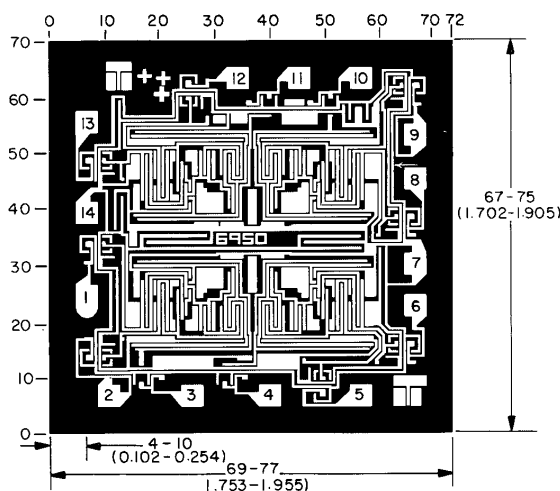


FIGURE 9. TYPICAL DYNAMIC POWER DISSIPATION AS A FUNCTION OF INPUT FREQUENCY

### Chip Dimensions and Pad Layout



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils ( $10^{-3}$  inch)

**METALLIZATION:** Thickness:  $11\text{k}\text{\AA} - 14\text{k}\text{\AA}$ , AL.

**PASSIVATION:**  $10.4\text{k}\text{\AA} - 15.6\text{k}\text{\AA}$ , Silane

**BOND PADS:** 0.004 inches X 0.004 inches MIN

**DIE THICKNESS:** 0.0198 inches - 0.0218 inches

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